

## RJK5015DPM

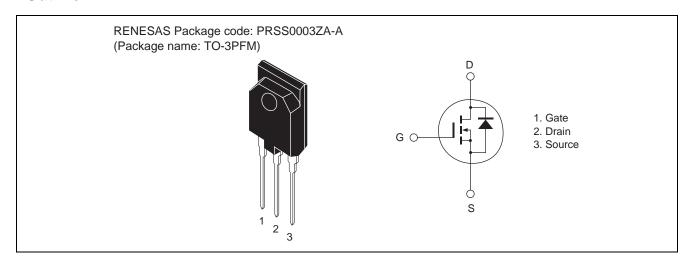
# Silicon N Channel MOS FET High Speed Power Switching

REJ03G1753-0100 Rev.1.00 Oct 26, 2009

#### **Features**

- Low on-resistance
- Low leakage current
- High speed switching

#### **Outline**



#### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

| Item  | Symbol                        | Ratings     | Unit |
|---|-------------------------------|-------------|------|
| Drain to source voltage                     | V <sub>DSS</sub>              | 500         | V    |
| Gate to source voltage                      | $V_{GSS}$                     | ±30         | V    |
| Drain current                               | I <sub>D</sub> Note4          | 25          | А    |
| Drain peak current                          | I <sub>D (pulse)</sub> Note1  | 75          | А    |
| Body-drain diode reverse drain current      | I <sub>DR</sub>               | 25          | А    |
| Body-drain diode reverse drain peak current | I <sub>DR (pulse)</sub> Note1 | 75          | А    |
| Avalanche current                           | I <sub>AP</sub> Note3         | 7           | А    |
| Avalanche energy                            | E <sub>AR</sub> Note3         | 2.7         | mJ   |
| Channel dissipation                         | Pch Note2                     | 60          | W    |
| Channel to case thermal impedance           | θch-c                         | 2.08        | °C/W |
| Channel temperature                         | Tch                           | 150         | °C   |
| Storage temperature                         | Tstg                          | -55 to +150 | °C   |

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tc = 25°C
- 3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C
- 4. Limited by maximum safe operation area

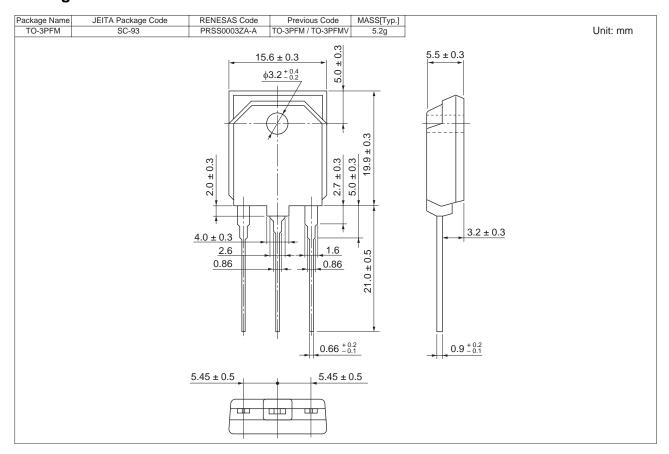
### **Electrical Characteristics**

 $(Ta = 25^{\circ}C)$ 

| Item                                       | Symbol              | Min | Тур  | Max  | Unit | Test conditions  |
|--|---------------------|-----|------|------|------|--|
| Drain to source breakdown voltage          | $V_{(BR)DSS}$       | 500 | _    | _    | V    | $I_D = 10 \text{ mA}, V_{GS} = 0$  |
| Zero gate voltage drain current            | I <sub>DSS</sub>    | _   | _    | 1    | μΑ   | $V_{DS} = 500 \text{ V}, V_{GS} = 0$                                     |
| Gate to source leak current                | I <sub>GSS</sub>    | _   | _    | ±0.1 | μΑ   | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$                                  |
| Gate to source cutoff voltage              | $V_{GS(off)}$       | 3.0 | _    | 4.5  | V    | $V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$                            |
| Static drain to source on state resistance | R <sub>DS(on)</sub> | _   | 0.21 | 0.24 | Ω    | $I_D = 12.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note5}}$             |
| Input capacitance                          | Ciss                | _   | 2600 | _    | pF   | V <sub>DS</sub> = 25 V   |
| Output capacitance                         | Coss                | _   | 270  | _    | pF   | $V_{GS} = 0$   |
| Reverse transfer capacitance               | Crss                | _   | 32   | _    | pF   | f = 1 MHz  |
| Turn-on delay time                         | $t_{d(on)}$         | _   | 42   | _    | ns   | I <sub>D</sub> = 12.5 A  |
| Rise time                                  | t <sub>r</sub>      | _   | 59   | _    | ns   | V <sub>GS</sub> = 10 V   |
| Turn-off delay time                        | $t_{d(off)}$        | _   | 103  | _    | ns   | $R_L = 20 \Omega$  |
| Fall time                                  | t <sub>f</sub>      | _   | 45   | _    | ns   | $Rg = 10 \Omega$   |
| Total gate charge                          | Qg                  | _   | 66   | _    | nC   | V <sub>DD</sub> = 400 V  |
| Gate to source charge                      | Qgs                 | _   | 14   | _    | nC   | V <sub>GS</sub> = 10 V   |
| Gate to drain charge                       | Qgd                 | _   | 29   | _    | nC   | I <sub>D</sub> = 25 A  |
| Body-drain diode forward voltage           | $V_{DF}$            | _   | 0.96 | 1.60 | V    | I <sub>F</sub> = 25 A, V <sub>GS</sub> = 0 Note5                         |
| Body-drain diode reverse recovery time     | t <sub>rr</sub>     | _   | 380  | _    | ns   | $I_F = 25 \text{ A}, V_{GS} = 0$<br>di <sub>F</sub> /dt = 100 A/ $\mu$ s |

Notes: 5. Pulse test

### **Package Dimensions**



### **Ordering Information**

| Part No.         | Quantity | Shipping Container |
|------------------|----------|--------------------|
| RJK5015DPM-00-T1 | 360 pcs  | Box (Tube)         |

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